



Bipolar NPN Bare Die – BTN6064

Part Description

The BTN6064 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications. PNP Complement is BTP6094.

Key Parameters:

- VCBO = 180V
- VCEO = 160V
- VEBO = 6V
- hFE = 72-330 @ VCE = 5V, IC = 0.01A
- VCE(Sat) = 0.2V @ IC = 0.05A, IB = 5mA
- fT = 300 MHz @ VCE = 10V, IE = 0A
- COBO = 0pF @ VCB = 6V

Features

Low VCE(sat). Designed to provide performance equivalent to ON Semi 2N5551

Die Size (Unawn)

400µm X 400µm, 16 Mils X 16 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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